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Inclosure Material: Metal Overall Length: 1.573 inches Terminal Length: 0.500 inches Overall Height: 0.500 inches Overall Height: 0.360 inches Overall Width: 1.056 inches Mounting Facility Quantity: 2 Internal Configuration: Junction contact-darlington connected Electrode Internally-electrically Connected To Case: Collector Mounting Method: Unthreaded hole Semiconductor Material: Silicon Voltage Rating In Volts Per Characteristic: 100.0 collector to base voltage/static/emitter open and 7.0 emitter to base voltage, static, collector open and 100.0 collector to emitter voltage/static/base open Current Rating Per Characteristic: 20.00 amperes source cutoff current and 0.50 amperes source cutoff current
Overall Length: 1.573 inches Terminal Length: 0.500 inches Overall Height: 0.360 inches Overall Width: 1.050 inches Mounting Facility Quantity: 2 Internal Configuration: Junction contact-darlington connected Electrode Internally-electrically Connected To Case: Collector Mounting Method: Unthreaded hole Semiconductor Material: Silicon Voltage Rating In Volts Per Characteristic: 100.0 collector to base voltage/static/emitter open and 7.0 emitter to base voltage, static, collector open and 100.0 collector to emitter voltage/static/base open Current Rating Per Characteristic:
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Current Rating Per Characteristic:
20.00 amperes source cutoff current and 0.50 amperes source cutoff current
Power Rating Per Characteristic:
175.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
1 case and 2 uninsulated wire lead
Specification Data:
81349-mil-s-19500/504 government specification
Shelf Life:
N/a
Unit Of Measure:

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Demilitarization:

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